

Amendments to the Claims

This listing of claims replaces all prior versions and listings of claims in the application.

Listing of Claims

1-9. (Canceled)

10. (Previously Presented) A semiconductor device comprising:  
a first wiring line formed over a substrate, the first wiring line comprising at least a first portion and a second portion;  
where second portion is not directly connected to the first portion;  
a second wiring line formed over the first wiring line with an insulating film interposed therebetween,  
wherein the first wiring line is formed on a same layer as a gate electrode of a thin film transistor,  
wherein the first wiring line and the second wiring line extend in parallel with each other,  
wherein the first portion of the first wiring line and the second wiring line are electrically connected with each other via a plurality of contact holes opened in the insulating film, and  
wherein the second portion of the first wiring line and the second wiring line are electrically connected with each other via a plurality of contact holes opened in the insulating film.

11. (Previously Presented) A semiconductor device according to claim 10, wherein the insulating film comprises an organic resin film selected from the group consisting of polyimide, polyamide, polyimideamide, and acrylic.

12. (Previously Presented) A semiconductor device according to claim 10, wherein the insulating film comprises silicon nitride.

13. (Previously Presented) A semiconductor device according to claim 10, wherein the insulating film comprises an interlayer insulating film.

14. (Previously Presented) A semiconductor device according to claim 10, wherein the first wiring line comprises at least one selected from the group consisting of aluminum, tantalum, polycrystalline silicon, and tungsten silicide.

15. (Previously Presented) A semiconductor device according to claim 10, wherein the second wiring line comprises aluminum.

16. (Previously Presented) A semiconductor device comprising:  
a first wiring line formed over a substrate, the first wiring line comprising at least a first portion and a second portion;  
an insulating film formed over the first wiring line;  
a second wiring line formed over the first wiring line with the insulating film interposed therebetween such that at least a portion of the second wiring line overlaps with the first wiring line; and  
a third wiring line formed on a same surface as the first wiring line and extending between the first and second portions of the first wiring line and across the second wiring line, wherein the insulating film is interposed between the third wiring line and the second wiring line,  
wherein the first wiring line is formed on a same layer as a gate electrode of a thin film transistor,  
wherein the first wiring line and the second wiring line extend in parallel with each other, wherein the first portion of the first wiring line and the second wiring line are electrically connected with each other via a plurality of contact holes opened in the insulating film, and

wherein the second portion of the first wiring line and the second wiring line are electrically connected with each other via a plurality of contact holes opened in the insulating film.

17. (Previously Presented) A semiconductor device according to claim 16, wherein the insulating film comprises an organic resin film selected from the group consisting of polyimide, polyamide, polyimideamide, and acrylic.

18. (Previously Presented) A semiconductor device according to claim 16, wherein the insulating film comprises silicon nitride.

19. (Previously Presented) A semiconductor device according to claim 16, wherein the insulating film comprises an interlayer insulating film.

20. (Previously Presented) A semiconductor device according to claim 16, wherein the first wiring line comprises at least one selected from the group consisting of aluminum, tantalum, polycrystalline silicon, and tungsten silicide.

21. (Previously Presented) A semiconductor device according to claim 16, wherein the second wiring line comprises aluminum.

22. (Previously Presented) A semiconductor device comprising:  
a first wiring line formed over a substrate, the first wiring line comprising at least a first portion and a second portion;  
an insulating film formed over the first wiring line;  
a second wiring line formed over the first wiring line with the insulating film interposed therebetween such that at least a portion of the second wiring line overlaps with the first wiring line; and

a third wiring line formed on a same surface as the first wiring line and extending between the first and second portions of the first wiring line and across the second wiring line, wherein the insulating film is interposed between the third wiring line and the second wiring line,

wherein the second wiring line is formed on a same layer as a source or a drain electrode of a thin film transistor,

wherein the first wiring line and the second wiring line extend in parallel with each other, wherein the first portion of the first wiring line and the second wiring line are electrically connected with each other via a plurality of contact holes opened in the insulating film, and

wherein the second portion of the first wiring line and the second wiring line are electrically connected with each other via a plurality of contact holes opened in the insulating film.

23. (Previously Presented) A semiconductor device according to claim 22, wherein the insulating film comprises an organic resin film selected from the group consisting of polyimide, polyamide, polyimideamide, and acrylic.

24. (Previously Presented) A semiconductor device according to claim 22, wherein the insulating film comprises silicon nitride.

25. (Previously Presented) A semiconductor device according to claim 22, wherein the insulating film comprises an interlayer insulating film.

26. (Previously Presented) A semiconductor device according to claim 22, wherein the first wiring line comprises at least one selected from the group consisting of aluminum, tantalum, polycrystalline silicon, and tungsten silicide.

27. (Previously Presented) A semiconductor device according to claim 22, wherein the second wiring line comprises aluminum.

28. (Previously Presented) A semiconductor device comprising:  
a first wiring line formed over a substrate, the first wiring line comprising at least a first portion and a second portion;  
a second wiring line formed over the first wiring line with an insulating film interposed therebetween such that at least a portion of the second wiring line overlaps with the first wiring line, and  
a third wiring line formed on a same surface as the first wiring line and extending between the first and second portions of the first wiring line and across the second wiring line, wherein the insulating film is interposed between the third wiring line and the second wiring line,  
wherein the first wiring line is formed on a same layer as a gate electrode of a thin film transistor,  
wherein the second wiring line is along a lengthwise direction of the first wiring line,  
wherein the first portion of the first wiring line and the second wiring line are electrically connected with each other via a plurality of contact holes opened in the insulating film, and  
wherein the second portion of the first wiring line and the second wiring line are electrically connected with each other via a plurality of contact holes opened in the insulating film.

29. (Previously Presented) A semiconductor device according to claim 28, wherein the insulating film comprises an organic resin film selected from the group consisting of polyimide, polyamide, polyimideamide, and acrylic.

30. (Previously Presented) A semiconductor device according to claim 28, wherein the insulating film comprises silicon nitride.

31. (Previously Presented) A semiconductor device according to claim 28, wherein the insulating film comprises an interlayer insulating film.

32. (Previously Presented) A semiconductor device according to claim 28, wherein the first wiring line comprises at least one selected from the group consisting of aluminum, tantalum, polycrystalline silicon, and tungsten silicide.

33. (Previously Presented) A semiconductor device according to claim 28, wherein the second wiring line comprises aluminum.

34. (Previously Presented) A semiconductor device comprising:  
a first wiring line formed over a substrate, the first wiring line comprising at least a first portion and a second portion;  
a second wiring line formed over the first wiring line with an insulating film interposed therebetween such that at least a portion of the second wiring line overlaps with the first wiring line, and  
a third wiring line formed on a same surface as the first wiring line and extending between the first and second portions of the first wiring line and across the second wiring line, wherein the insulating film is interposed between the third wiring line and the second wiring line,  
wherein one of the first wiring line and the second wiring line is formed on a same layer as a source or a drain electrode of a thin film transistor,  
wherein the second wiring line is along a lengthwise direction of the first wiring line,  
wherein the first portion of the first wiring line and the second wiring line are electrically connected with each other via a plurality of contact holes opened in the insulating film, and

wherein the second portion of the first wiring line and the second wiring line are electrically connected with each other via a plurality of contact holes opened in the insulating film.

35. (Previously Presented) A semiconductor device according to claim 34, wherein the insulating film comprises an organic resin film selected from the group consisting of polyimide, polyamide, polyimideamide, and acrylic.

36. (Previously Presented) A semiconductor device according to claim 34, wherein the insulating film comprises silicon nitride.

37. (Previously Presented) A semiconductor device according to claim 34, wherein the insulating film comprises an interlayer insulating film.

38. (Previously Presented) A semiconductor device according to claim 34, wherein the first wiring line comprises at least one selected from the group consisting of aluminum, tantalum, polycrystalline silicon, and tungsten silicide.

39. (Previously Presented) A semiconductor device according to claim 34, wherein the second wiring line comprises aluminum.

40. (Previously Presented) A semiconductor device comprising:  
a first wiring line formed over a substrate, the first wiring line comprising at least a first portion and a second portion;  
where second portion is not directly connected to the first portion;  
a second wiring line formed over the first wiring line with an insulating film interposed therebetween,

wherein one of the first wiring line and the second wiring line is formed on a same layer as a source or a drain electrode of a thin film transistor,

wherein the first wiring line and the second wiring line extend in parallel with each other,

wherein the first portion of the first wiring line and the second wiring line are electrically connected with each other via a plurality of contact holes opened in the insulating film, and

wherein the second portion of the first wiring line and the second wiring line are electrically connected with each other via a plurality of contact holes opened in the insulating film.

41. (Previously Presented) A semiconductor device according to claim 40, wherein the insulating film comprises an organic resin film selected from the group consisting of polyimide, polyamide, polyimideamide, and acrylic.

42. (Previously Presented) A semiconductor device according to claim 40, wherein the insulating film comprises silicon nitride.

43. (Previously Presented) A semiconductor device according to claim 40, wherein the insulating film comprises an interlayer insulating film.

44. (Previously Presented) A semiconductor device according to claim 40, wherein the first wiring line comprises at least one selected from the group consisting of aluminum, tantalum, polycrystalline silicon, and tungsten silicide.

45. (Previously Presented) A semiconductor device according to claim 40, wherein the second wiring line comprises aluminum.

46. (Previously Presented) A semiconductor device according to claim 10, wherein the semiconductor device is a liquid crystal display device or an electroluminescence display device.



47. (Previously Presented) A semiconductor device according to claim 16, wherein the semiconductor device is a liquid crystal display device or an electroluminescence display device.

48. (Previously Presented) A semiconductor device according to claim 22, wherein the semiconductor device is a liquid crystal display device or an electroluminescence display device.

49. (Previously Presented) A semiconductor device according to claim 28, wherein the semiconductor device is a liquid crystal display device or an electroluminescence display device.

50. (Previously Presented) A semiconductor device according to claim 34, wherein the semiconductor device is a liquid crystal display device or an electroluminescence display device.

51. (Previously Presented) A semiconductor device according to claim 40, wherein the semiconductor device is a liquid crystal display device or an electroluminescence display device.

52. (Previously Presented) A semiconductor device according to claim 10, wherein the insulating film comprises silicon oxide.

53. (Previously Presented) A semiconductor device according to claim 16, wherein the insulating film comprises silicon oxide.

54. (Previously Presented) A semiconductor device according to claim 22, wherein the insulating film comprises silicon oxide.

55. (Previously Presented) A semiconductor device according to claim 28, wherein the insulating film comprises silicon oxide.

56. (Previously Presented) A semiconductor device according to claim 34, wherein the insulating film comprises silicon oxide.

57. (Previously Presented) A semiconductor device according to claim 40, wherein the insulating film comprises silicon oxide.

58. (Previously Presented) A semiconductor device according to claim 10, wherein the insulating film is a laminate film.

59. (Previously Presented) A semiconductor device according to claim 16, wherein the insulating film is a laminate film.

60. (Previously Presented) A semiconductor device according to claim 22, wherein the insulating film is a laminate film.

61. (Previously Presented) A semiconductor device according to claim 28, wherein the insulating film is a laminate film.

62. (Previously Presented) A semiconductor device according to claim 34, wherein the insulating film is a laminate film.

63. (Previously Presented) A semiconductor device according to claim 40, wherein the insulating film is a laminate film.

64. (New) A semiconductor device comprising:  
a first wiring line formed over a substrate, the first wiring line comprising at least a first portion and a second portion;  
where second portion is not directly connected to the first portion;

a second wiring line formed over the first wiring line with an insulating film interposed therebetween,

wherein the first wiring line is formed from a same conductive layer as a gate electrode of a thin film transistor,

wherein the first wiring line and the second wiring line extend in parallel with each other,

wherein the first portion of the first wiring line and the second wiring line are electrically connected with each other via a plurality of contact holes opened in the insulating film, and

wherein the second portion of the first wiring line and the second wiring line are electrically connected with each other via a plurality of contact holes opened in the insulating film.

65. (New) A semiconductor device according to claim 64, wherein the insulating film comprises an organic resin film selected from the group consisting of polyimide, polyamide, polyimideamide, and acrylic.

66. (New) A semiconductor device according to claim 64, wherein the insulating film comprises silicon nitride.

67. (New) A semiconductor device according to claim 64, wherein the insulating film comprises an interlayer insulating film.

68. (New) A semiconductor device according to claim 64, wherein the first wiring line comprises at least one selected from the group consisting of aluminum, tantalum, polycrystalline silicon, and tungsten silicide.

69. (New) A semiconductor device according to claim 64, wherein the second wiring line comprises aluminum.

70. (New) A semiconductor device comprising:  
a first wiring line formed over a substrate, the first wiring line comprising at least a first portion and a second portion;  
an insulating film formed over the first wiring line;  
a second wiring line formed over the first wiring line with the insulating film interposed therebetween such that at least a portion of the second wiring line overlaps with the first wiring line; and  
a third wiring line formed on a same surface as the first wiring line and extending between the first and second portions of the first wiring line and across the second wiring line, wherein the insulating film is interposed between the third wiring line and the second wiring line,  
wherein the first wiring line is formed from a same conductive layer as a gate electrode of a thin film transistor,  
wherein the first wiring line and the second wiring line extend in parallel with each other,  
wherein the first portion of the first wiring line and the second wiring line are electrically connected with each other via a plurality of contact holes opened in the insulating film, and  
wherein the second portion of the first wiring line and the second wiring line are electrically connected with each other via a plurality of contact holes opened in the insulating film.

71. (New) A semiconductor device according to claim 70, wherein the insulating film comprises an organic resin film selected from the group consisting of polyimide, polyamide, polyimideamide, and acrylic.

72. (New) A semiconductor device according to claim 70, wherein the insulating film comprises silicon nitride.

73. (New) A semiconductor device according to claim 70, wherein the insulating film comprises an interlayer insulating film.

74. (New) A semiconductor device according to claim 70, wherein the first wiring line comprises at least one selected from the group consisting of aluminum, tantalum, polycrystalline silicon, and tungsten silicide.

75. (New) A semiconductor device according to claim 70, wherein the second wiring line comprises aluminum.

76. (New) A semiconductor device comprising:  
a first wiring line formed over a substrate, the first wiring line comprising at least a first portion and a second portion;  
an insulating film formed over the first wiring line;  
a second wiring line formed over the first wiring line with the insulating film interposed therebetween such that at least a portion of the second wiring line overlaps with the first wiring line; and  
a third wiring line formed on a same surface as the first wiring line and extending between the first and second portions of the first wiring line and across the second wiring line,  
wherein the insulating film is interposed between the third wiring line and the second wiring line,  
wherein the second wiring line is formed from a same conductive layer as a source or a drain electrode of a thin film transistor,  
wherein the first wiring line and the second wiring line extend in parallel with each other,  
wherein the first portion of the first wiring line and the second wiring line are electrically connected with each other via a plurality of contact holes opened in the insulating film, and

wherein the second portion of the first wiring line and the second wiring line are electrically connected with each other via a plurality of contact holes opened in the insulating film.

77. (New) A semiconductor device according to claim 76, wherein the insulating film comprises an organic resin film selected from the group consisting of polyimide, polyamide, polyimideamide, and acrylic.

78. (New) A semiconductor device according to claim 76, wherein the insulating film comprises silicon nitride.

79. (New) A semiconductor device according to claim 76, wherein the insulating film comprises an interlayer insulating film.

80. (New) A semiconductor device according to claim 76, wherein the first wiring line comprises at least one selected from the group consisting of aluminum, tantalum, polycrystalline silicon, and tungsten silicide.

81. (New) A semiconductor device according to claim 76, wherein the second wiring line comprises aluminum.

82. (New) A semiconductor device comprising:  
a first wiring line formed over a substrate, the first wiring line comprising at least a first portion and a second portion;  
a second wiring line formed over the first wiring line with an insulating film interposed therebetween such that at least a portion of the second wiring line overlaps with the first wiring line, and

a third wiring line formed on a same surface as the first wiring line and extending between the first and second portions of the first wiring line and across the second wiring line, wherein the insulating film is interposed between the third wiring line and the second wiring line,

wherein the first wiring line is formed from a same conductive layer as a gate electrode of a thin film transistor,

wherein the second wiring line is along a lengthwise direction of the first wiring line,

wherein the first portion of the first wiring line and the second wiring line are electrically connected with each other via a plurality of contact holes opened in the insulating film, and

wherein the second portion of the first wiring line and the second wiring line are electrically connected with each other via a plurality of contact holes opened in the insulating film.

83. (New) A semiconductor device according to claim 82, wherein the insulating film comprises an organic resin film selected from the group consisting of polyimide, polyamide, polyimideamide, and acrylic.

84. (New) A semiconductor device according to claim 82, wherein the insulating film comprises silicon nitride.

85. (New) A semiconductor device according to claim 82, wherein the insulating film comprises an interlayer insulating film.

86. (New) A semiconductor device according to claim 82, wherein the first wiring line comprises at least one selected from the group consisting of aluminum, tantalum, polycrystalline silicon, and tungsten silicide.

87. (New) A semiconductor device according to claim 82, wherein the second wiring line comprises aluminum.

88. (New) A semiconductor device comprising:  
a first wiring line formed over a substrate, the first wiring line comprising at least a first portion and a second portion;  
a second wiring line formed over the first wiring line with an insulating film interposed therebetween such that at least a portion of the second wiring line overlaps with the first wiring line, and  
a third wiring line formed on a same surface as the first wiring line and extending between the first and second portions of the first wiring line and across the second wiring line, wherein the insulating film is interposed between the third wiring line and the second wiring line,  
wherein one of the first wiring line and the second wiring line is formed from a same conductive layer as a source or a drain electrode of a thin film transistor,  
wherein the second wiring line is along a lengthwise direction of the first wiring line,  
wherein the first portion of the first wiring line and the second wiring line are electrically connected with each other via a plurality of contact holes opened in the insulating film, and  
wherein the second portion of the first wiring line and the second wiring line are electrically connected with each other via a plurality of contact holes opened in the insulating film.

89. (New) A semiconductor device according to claim 88, wherein the insulating film comprises an organic resin film selected from the group consisting of polyimide, polyamide, polyimideamide, and acrylic.

90. (New) A semiconductor device according to claim 88, wherein the insulating film comprises silicon nitride.



91. (New) A semiconductor device according to claim 88, wherein the insulating film comprises an interlayer insulating film.

92. (New) A semiconductor device according to claim 88, wherein the first wiring line comprises at least one selected from the group consisting of aluminum, tantalum, polycrystalline silicon, and tungsten silicide.

93. (New) A semiconductor device according to claim 88, wherein the second wiring line comprises aluminum.

94. (New) A semiconductor device comprising:  
a first wiring line formed over a substrate, the first wiring line comprising at least a first portion and a second portion;  
where second portion is not directly connected to the first portion;  
a second wiring line formed over the first wiring line with an insulating film interposed therebetween,  
wherein one of the first wiring line and the second wiring line is formed from a same conductive layer as a source or a drain electrode of a thin film transistor,  
wherein the first wiring line and the second wiring line extend in parallel with each other,  
wherein the first portion of the first wiring line and the second wiring line are electrically connected with each other via a plurality of contact holes opened in the insulating film, and  
wherein the second portion of the first wiring line and the second wiring line are electrically connected with each other via a plurality of contact holes opened in the insulating film.

95. (New) A semiconductor device according to claim 94, wherein the insulating film comprises an organic resin film selected from the group consisting of polyimide, polyamide, polyimideamide, and acrylic.

96. (New) A semiconductor device according to claim 94, wherein the insulating film comprises silicon nitride.

97. (New) A semiconductor device according to claim 94, wherein the insulating film comprises an interlayer insulating film.

98. (New) A semiconductor device according to claim 94, wherein the first wiring line comprises at least one selected from the group consisting of aluminum, tantalum, polycrystalline silicon, and tungsten silicide.

99. (New) A semiconductor device according to claim 94, wherein the second wiring line comprises aluminum.

100. (New) A semiconductor device according to claim 64, wherein the semiconductor device is a liquid crystal display device or an electroluminescence display device.

101. (New) A semiconductor device according to claim 70, wherein the semiconductor device is a liquid crystal display device or an electroluminescence display device.

102. (New) A semiconductor device according to claim 76, wherein the semiconductor device is a liquid crystal display device or an electroluminescence display device.

103. (New) A semiconductor device according to claim 82, wherein the semiconductor device is a liquid crystal display device or an electroluminescence display device.

104. (New) A semiconductor device according to claim 88, wherein the semiconductor device is a liquid crystal display device or an electroluminescence display device.

105. (New) A semiconductor device according to claim 94, wherein the semiconductor device is a liquid crystal display device or an electroluminescence display device.

106. (New) A semiconductor device according to claim 64, wherein the insulating film comprises silicon oxide.

107. (New) A semiconductor device according to claim 70, wherein the insulating film comprises silicon oxide.

108. (New) A semiconductor device according to claim 76, wherein the insulating film comprises silicon oxide.

109. (New) A semiconductor device according to claim 82, wherein the insulating film comprises silicon oxide.

110. (New) A semiconductor device according to claim 88, wherein the insulating film comprises silicon oxide.

111. (New) A semiconductor device according to claim 94, wherein the insulating film comprises silicon oxide.

112. (New) A semiconductor device according to claim 64, wherein the insulating film is a laminate film.

113. (New) A semiconductor device according to claim 70, wherein the insulating film is a laminate film.

114. (New) A semiconductor device according to claim 76, wherein the insulating film is a laminate film.

115. (New) A semiconductor device according to claim 82, wherein the insulating film is a laminate film.

116. (New) A semiconductor device according to claim 88, wherein the insulating film is a laminate film.

117. (New) A semiconductor device according to claim 94, wherein the insulating film is a laminate film.